metal layer is made of one of aluminum, an aluminum alloy, AlNd, copper and a copper alloy, and the second metal layer is made of one of Cr, Cr-alloy, Mo, Mo-alloy, Ta, Ta-alloy, W, and W-alloy.--

Please replace the paragraph beginning on page 5, line 17, with the following rewritten paragraph:

--The electrode line may have first, second and third metal layers of a three-layered structure, and a side portion of the second metal layer is less etched to protrude beyond that of the first and third metal layers.--

Please replace the paragraph beginning on page 6, line 19, with the following rewritten paragraph:

--Figs. 4A and 4B are cross-sectional views illustrating a method of forming an electrode line 51 and an insulating layer 54. First, as shown in Fig. 4A, first and second metal layers 50 and 52 are sequentially deposited on a substrate 1 and then are patterned into a wire electrode 51 of a dual-layered structure. The first metal layer 50 is made of a low resistive metal such as an aluminum-based metal and a copper-based metal. The second metal layer 52 is made of a material having a high corrosion resistance, for example, Cr, Mo, Ta, W, or their alloy.--

Please replace the paragraph beginning on page 7, line 7, with the following rewritten paragraph:

--The electrode line 51 has an overhang portion due to a difference of an etching rate between the first and second metal

layers 50 and 52. In the conventional art, in order to remove the overhang portion, the dry-etching process is additionally performed. In order to insulate the electrode line, an inorganic insulating layer made of SiNx or SiO_2 is formed. However, in the preferred embodiment of the present invention, in order to insulate the electrode line 51 having the overhang portion, an organic insulating layer 54 is applied using a coating technique, and therefore it is easy to form the organic insulating layer 54 compared with the conventional art using a vacuum deposition technique. Further, since the organic insulating layer 54 is excellent in flatness and has a dielectric constant of less than 3(three), there is an advantage that an aperture ratio of a liquid crystal display device can be improved.--

Please replace the paragraph beginning on page 8, line 3, with the following rewritten paragraph:

--Fig. 5 is a cross-sectional view illustrating a method of forming an organic insulating layer when a wire electrode of a three-layered structure is formed according to the preferred embodiment of the present invention. As shown in Fig. 5, a first metal layer 60 is formed on a substrate 1, and a second metal layer 62 is formed on the first metal layer 60. Further, a third metal layer 64 is formed on the second metal layer 62. An organic insulating layer 54 is formed over the whole surface of the substrate 1 while covering the first, second and third metal layers

60, 62 and 64. The first and third metal layers 60 and 64 is made of a low resistive material such as an aluminum-based metal or a copper-based metal. The second metal layer 62 is made of a material having high corrosion resistance such as Cr, Mo, Ta, W, or their alloys.--

Please replace the paragraph beginning on page 8, line 22, with the following rewritten paragraph:

--Even though not shown, the organic insulating layer according to the preferred embodiment of the present invention can be applied to a method of manufacturing an electrode line having no overhang but a taper angle of more than 45° from a top surface of the electrode line. In other words, when the electrode line is a single-layered structure and has a taper angle of more than 45°, it is preferable that the organic insulating layer is formed as an insulating layer for insulating the electrode line. Therefore, defects such as a line open can be prevented.--

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A method of manufacturing an array substrate, comprising:

forming an electrode line on a substrate using a wet etching technique; and

forming an organic insulating layer on an exposed surface of